MH260 Hall-effect sensor is a temperature stable, stress-resistant, Low Tolerance of Sensitivity micro-power switch. Superior high-temperature performance is made possible through a dynamic offset cancellation that utilizes chopper-stabilization. This method reduces the offset voltage normally caused by device over molding, temperature dependencies, and thermal stress.

MH260 is special made for low operation voltage, 1.7V, to active the chip which is includes the following on a single silicon chip: voltage regulator, Hall voltage generator, small-signal amplifier, chopper stabilization, Schmitt trigger, CMOS output driver. Advanced CMOS wafer fabrication processing is used to take advantage of low-voltage requirements, component matching, very low input-offset errors, and small component geometries. This device requires the presence of omni-polar magnetic fields for operation.

The package type is in a Halogen Free version has been verified by third party Lab.

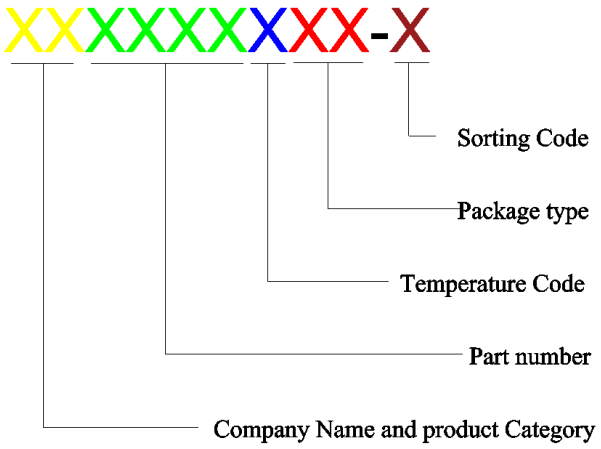
Features and Benefits

- CMOS Hall IC Technology
- Strong RF noise protection
- 1.7 to 5.5V for battery-powered applications
- Omni polar, output switches with absolute value of North or South pole from magnet
- Operation down to 1.7V, Micro power consumption
- High Sensitivity for reed switch replacement applications
- Multi Small Size option
- Low sensitivity drift in crossing of Temp. range
- Ultralow power consumption at 5uA (Avg)
- High ESD Protection, HBM>±4KV(min)
- Totem-pole output
- RoHS compliant 2011/65/EU and Halogen Free

Applications

- Solid state switch
- Handheld Wireless Handset Awake Switch (Flip Cell/PHS Phone/Note Book/Flip Video Set)
- Lid close sensor for battery powered devices
- Magnet proximity sensor for reed switch replacement in low duty cycle applications
- Water Meter
- Floating Meter
- PDVD
- NB

Ordering Information



Company Name and Product Category

MH:MST Hall Effect/MP:MST Power IC

Part number

181,182,183,184,185,248,249,276,477,381,381F,381R,382…..

If part # is just 3 digits, the forth digit will be omitted.

Temperature range

E: 85 ℃, I: 105 ℃, K: 125 ℃, L: 150 ℃

Package type

UA:TO-92S,VK:TO-92S(4pin),VF:TO-92S(5pin),SO:SOT-23,

SQ:QFN-3,ST:TSOT-23,SN:SOT-553,SF:SOT-89(5pin),

SS:TSOT-26,SD:DFN-6

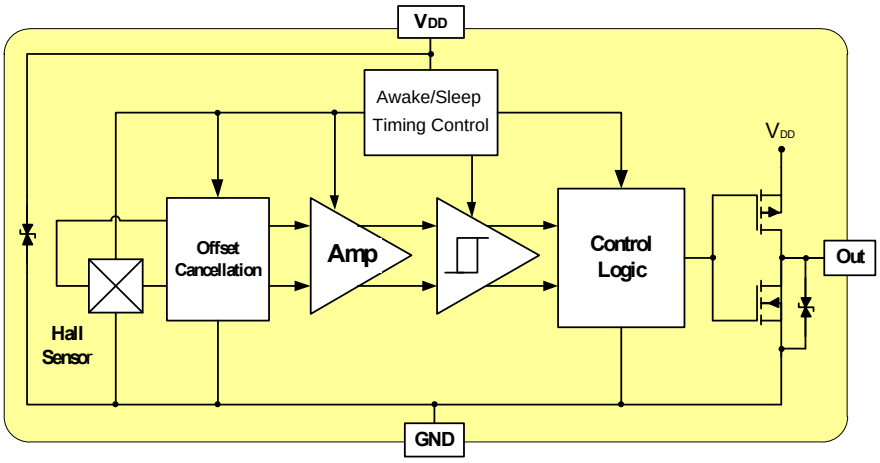
Sorting

α,β,Blank…..

Part No.	**Temperature Suffix**	**Package Type**
MH260ESS	E (-40°C to +85°C)	SS (QFN1x1-4L)

Custom sensitivity selection is available by MST sorting technology

Functional Diagram



***Note**: Static sensitive device; please observe ESD precautions. Reverse V_{DD} protection is not included. For reverse voltage protection, a 100Ω resistor in series with V_{DD} is recommended.*

MH260, HBM>±4KV which is verified by third party lab.

Absolute Maximum Ratings *At(Ta=25℃)*

Characteristics		Values	Unit
Supply voltage,(V_{DD})		6	V
Output Voltage,(V_{out})		6	V
Reverse Voltage , (V_{DD}) (V_{OUT})		-0.3	V
Magnetic flux density		Unlimited	Gauss
Output current,(I_{OUT})		5	mA
Operating temperature range, (Ta)		-40 to +85	℃
Storage temperature range, (Ts)		-65 to +150	℃
Maximum Junction Temp,(Tj)		150	℃
Thermal Resistance	(θ_{JA})SS	300	℃/W
	(θ_{JC})SS	52	℃/W
Package Power Dissipation, (P_D)SS		416	mW

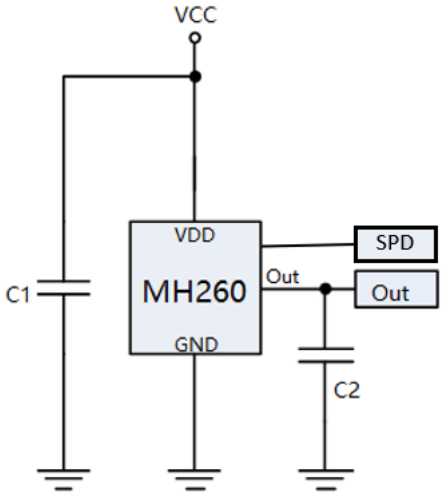
Note: *Exceeding the absolute maximum ratings may cause permanent damage. Exposure to absolute maximum-rated conditions for extended periods may affect device reliability.*

Electrical Specifications

DC Operating Parameters：Ta=25℃, V_{DD}=1.8V

Parameters		Test Conditions	Min	Typ	Max	Units
Supply Voltage,(V_{DD})		Operating	1.7		5.5	V
Supply Current,(I_{DD})		Awake State		1.4	3	mA
		Sleep State		3.6	7	μA
		Average（SPD=Lo）		5(350)	10(600)	μA
Output High Voltage,(V_{OH})		I_{OUT}=0.5mA(Source)	VDD-0.2			V
Output Low Voltage,(V_{OL})		I_{OUT}=0.5mA(Sink)			0.2	V
Awake mode time,(T_{aw})		Operating		40	80	uS
Sleep mode time,(T_{SL})		Operating(SPD=Lo)		40(0.16)	80(0.32)	mS
Duty Cycle,(D,C)		SPD=Open (SPD=Lo)		0.1(25)		%
Output High Voltage,(V_{OH})		I_{OUT}=0.5mA(Source)	VDD-0.2			V
Power-On Time,(Tpo)				40	80	mS
Output Switch Time,(Tsw)				80	160	mS
Output Switch Frequency,(Fsw)		SPD=Open(SPD=Lo)	10(2000)			Hz
Electro-Static Discharge		HBM	4			KV
Operate Point	(B_{OPS})	S pole to branded side, B > B_{OP}, Vout On	20	30	40	Gauss
	(B_{OPN})	N pole to branded side, B > B_{OP}, Vout On	-40	-30	-20	Gauss
Release Point	(B_{RPS})	S pole to branded side, B < B_{RP}, Vout Off	10	20	30	Gauss
	(B_{RPN})	N pole to branded side, B < B_{RP}, Vout Off	-30	-20	-10	Gauss
Hysteresis,(BHYS)		|BOPx - BRPx|		10		Gauss

Typical Application circuit

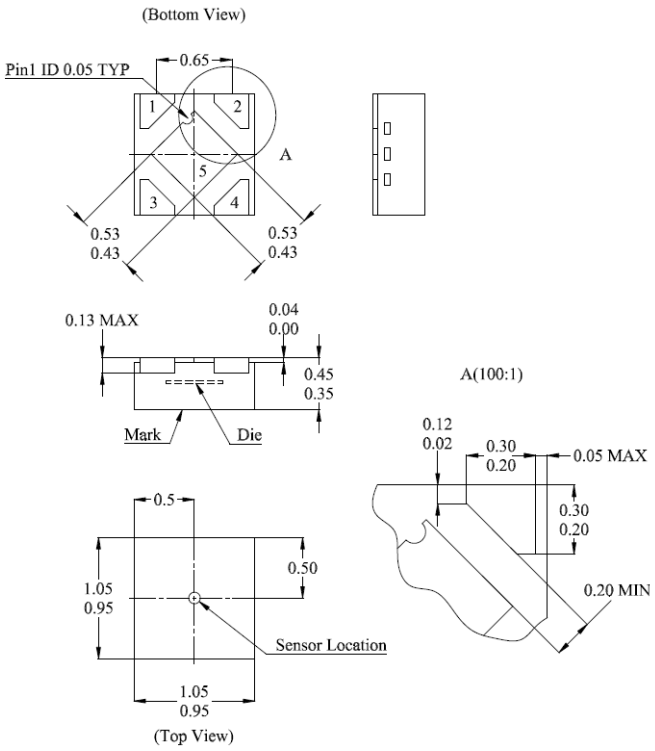


C1：10nF

C2：100pF

Sensor Location, package dimension and marking

SS Package (DFN 1.0*1.0)



NOTES:

1. Controlling dimension: mm
2. Leads must be free of flash and plating voids
3. Lead thickness after solder plating will be 0.254mm maximum
4. PINOUT:

Pin No.	Pin Name	Function
1	V_{DD}	Power Supply
2	GND	Ground
3	SPD	Set pin
4	V_{OUT}	Output
5	N.C	Heat sink[*1]

5. (For reference only)Land Pattern